L Number	Hits	Search Text	DB	Time stamp
1	49892	isotrop\$5	USPAT;	2004/06/17 18:43
-			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	3802	l adj shap\$2 same spacer\$1	USPAT;	2004/06/17 18:45
!			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
i			IBM_TDB	
3	4822		USPAT;	2004/06/17 18:43
		(438/232) or (438/301) or (438/303) or	US-PGPUB;	
		(438/305) or (438/306) or (438/307) or (438/595)).CCLS.	EPO; JPO; DERWENT;	
		(436/393)).ССЦЗ.	IBM TDB	1
4	13856	isotrop\$5 near5 etch\$3	USPAT;	2004/06/17 18:44
-	13030	130clop43 hear3 ecen43	US-PGPUB;	2004/00/1/ 10:41
			EPO; JPO;	
1			DERWENT;	
]			IBM TDB	
5	52320	(isotrop\$5 or wet) near5 etch\$3	USPAT;	2004/06/17 18:48
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	54	((isotrop\$5 or wet) near5 etch\$3) same (l	USPAT;	2004/06/17 18:44
		adj shap\$2 same spacer\$1)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_		*-	IBM_TDB	
7	346624	spacer\$1	USPAT;	2004/06/17 18:45
			US-PGPUB;	
			EPO; JPO;	
,			DERWENT; IBM TDB	
8	3851	((isotrop\$5 or wet) near5 etch\$3) same	USPAT;	2004/06/17 18:45
	3031	spacer\$1	US-PGPUB;	2004/00/17 18:45
		bpace191	EPO; JPO;	
			DERWENT;	
			IBM TDB	
9	189323	l adj shap\$2	USPAT;	2004/06/17 18:46
			US-PGPUB;	' '
			EPO; JPO;	
		_	DERWENT;	
			IBM_TDB	
10	54	(((isotrop\$5 or wet) near5 etch\$3) same	USPAT;	2004/06/17 18:48
		spacer\$1) same (l adj shap\$2)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
11	23	((((isotrop\$5 or wet) near5 etch\$3) same	<pre>IBM_TDB USPAT;</pre>	2004/06/17 18:49
	23	spacer\$1) same (l adj shap\$2)) and	US-PGPUB;	2007/00/1/ 10:49
		((isotrop\$5 or wet) near5 etch\$3 near10	EPO; JPO;	
		nitride)	DERWENT;	
		· · · · · ·	IBM_TDB	
16	2	"6518136"	USPAT	2004/06/17 19:07
19	3	("5716862" "6025267" "6165826").PN.	USPAT	2004/06/17 19:12
20	13	("4038107" "4638347" "4697199"	USPAT	2004/06/17 19:35
		"4735680" "4764477" "4818714"		
	İ	"4843023" "4851730" "4853352"]	
		"4981810" "5183770" "5221632"		
		"5256586").PN.		
21	41	5573965.URPN.	USPAT	2004/06/17 19:35
-	0	((gate adj dielectric) with (semiconductor	USPAT;	2002/05/10 14:46
		adj substrate)) same ((gate adj electrode)	US-PGPUB;	
		with (gate adj dielectric) with	EPO; JPO;	
		(semiconductor adj sustrate))	DERWENT;	
			IBM_TDB	<u> </u>

-	319	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode)	USPAT; US-PGPUB;	2002/05/10 14:34
}		with (gate adj dielectric) with	EPO; JPO;	
		(semiconductor adj substrate))	DERWENT;	
1		,	IBM_TDB	
-	0	(((gate adj dielectric) with (semiconductor	USPĀT;	2002/05/10 14:06
		adj substrate)) same ((gate adj electrode)	US-PGPUB;	
		with (gate adj dielectric) with	EPO; JPO;	
		(semiconductor adj substrate))) and	DERWENT;	
		(extension adj control)	IBM_TDB	
-	147		USPAT;	2002/05/10 14:27
		adj substrate)) same ((gate adj electrode)	US-PGPUB;	
		with (gate adj dielectric) with	EPO; JPO;	
		(semiconductor adj substrate))) and (protective adj layer\$1 or (film\$1))	DERWENT; IBM TDB	
_		((((gate adj dielectric) with (semiconductor	USPAT;	2002/05/10 14:24
-	0	adj substrate)) same ((gate adj electrode)	US-PGPUB;	2002/03/10 14:21
		with (gate adj dielectric) with	EPO; JPO;	
		(semiconductor adj substrate))) and	DERWENT;	
		(extension adj control)) and (sidewall or	IBM TDB	
	-	(side adj wall) with protection)	_	
-	0	((((gate adj dielectric) with (semiconductor	USPAT;	2002/05/10 14:09
		adj substrate)) same ((gate adj electrode)	US-PGPUB;	
		with (gate adj dielectric) with	EPO; JPO;	
	İ	(semiconductor adj substrate))) and	DERWENT;	
		(extension adj control)) and (sidewall or	IBM_TDB	
		(side adj wall))		0000/05/10 14 11
-	12		USPAT;	2002/05/10 14:11
		adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with	US-PGPUB; EPO; JPO;	
		(semiconductor adj substrate))) and	DERWENT;	
		(protective adj layer\$1 or (film\$1))) and	IBM TDB	
		(first adj impurit\$3) and (second adj		
		impurit\$3)		
-	392	l •	USPAT;	2002/05/10 14:18
		adj substrate)) same ((gate adj electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/10 14 10
-	361		USPAT;	2002/05/10 14:19
		electrode)) with (semiconductor adj	US-PGPUB;	
		substrate)))	EPO; JPO; DERWENT;	
			IBM TDB	
-	333	(((gate adj dielectric) same (gate adj	USPAT;	2002/05/10 14:35
		electrode)) with (semiconductor adj	US-PGPUB;	
		substrate))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	333		USPAT;	2002/05/10 14:24
		electrode)) with (semiconductor adj	US-PGPUB;	
		substrate)	EPO; JPO;	
			DERWENT;	
	130	(((anto add diologhria) come (anto add	IBM_TDB USPAT:	2002/05/10 14:36
1 -	138	(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj	USPAT; US-PGPUB;	2002/05/10 14:36
		substrate)) and (sidewall or (side adj	EPO; JPO;	
1		wall))	DERWENT;	
!			IBM TDB	
-	72	((((gate adj dielectric) same (gate adj	USPAT;	2002/05/10 14:37
		electrode)) with (semiconductor adj	US-PGPUB;	·
		substrate)) and (sidewall or (side adj	EPO; JPO;	
'		wall))) and (protective adj layer\$1 or	DERWENT;	
		(film\$1))	IBM_TDB	
-	103052		USPAT;	2004/06/17 13:35
		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))	EPO; JPO;	
			DERWENT; IBM TDB	
L	L	L.,	מתו"ותם ד	L

-	53	((metal adj oxide adj field adj effect adj	USPAT;	2002/05/10 14:35
		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))) same ((gate adj dielectric) with	EPO; JPO; DERWENT;	
		(semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric)	IBM TDB	
		with (semiconductor adj substrate))	1501_155	
l _	62	((metal adj oxide adj field adj effect adj	USPAT;	2002/05/10 14:35
	02	transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))) same(((gate adj dielectric) same	EPO; JPO;	
		(gate adj electrode)) with (semiconductor	DERWENT;	
		adj substrate))	IBM_TDB	
-	0	((((metal adj oxide adj field adj effect adj	USPAT;	2002/05/10 14:38
		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))) same(((gate adj dielectric) same	EPO; JPO;	
		(gate adj electrode)) with (semiconductor	DERWENT;	
		adj substrate))) same (sidewall or (side adj wall))) same (protective adj layer\$1 or	IBM_TDB	
		(film\$1))		·
_	20	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2002/05/10 14:37
		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))) same(((gate adj dielectric) same	EPO; JPO;	
		(gate adj electrode)) with (semiconductor	DERWENT;	
		adj substrate))) and (sidewall or (side adj	IBM_TDB	
		wall))		
-	0	((((metal adj oxide adj field adj effect adj	USPAT;	2002/05/10 14:40
		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor	EPO; JPO; DERWENT;	
		adj substrate))) same (sidewall or (side	IBM TDB	
		adj wall))) and (protective adj layer\$1 or	12122	
		(film\$1))		
-	2	1 ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2002/05/10 14:49
		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	
		(MOSFET))) same(((gate adj dielectric) same	EPO; JPO;	
		(gate adj electrode)) with (semiconductor	DERWENT;	
		adj substrate))) same (sidewall or (side	IBM_TDB	
	2	<pre> adj wall)) ((((metal adj oxide adj field adj effect adj</pre>	USPAT;	2002/05/10 14:48
_		transistor\$1 or (MOS adj transistor\$1) or	US-PGPUB;	2002/03/10 14.40
		(MOSFET))) same(((gate adj dielectric) same	EPO; JPO;	
		(gate adj electrode)) with (semiconductor	DERWENT;	
		adj substrate))) same (sidewall or (side	IBM_TDB	
		adj wall))) and ((protective or (insulat\$3))		
		adj layer\$1 or (film\$1))		
-	6770	gate adj dielectric	USPAT;	2002/05/10 14:47
			US-PGPUB; EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	2280	(gate adj dielectric) same (gate adj	USPAT;	2002/05/10 14:48
İ		electrode)	US-PGPUB;	= - : • •
1			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	803	((gate adj dielectric) same (gate adj	USPAT;	2002/05/10 14:49
		electrode)) same ((protective or	US-PGPUB;	
}		(insulat\$3)) adj layer\$1 or (film\$1))	EPO; JPO; DERWENT;	
			IBM TDB	
_	138	(((gate adj dielectric) same (gate adj	USPAT;	2002/05/10 14:50
1		electrode)) same ((protective or	US-PGPUB;	
İ		(insulat\$3)) adj layer\$1 or (film\$1))) same	EPO; JPO;	
		(sidewall or (side adj wall))	DERWENT;	·
	[IBM_TDB	
-	7	(((((gate adj dielectric) same (gate adj	USPAT;	2002/05/10 14:53
İ	1	electrode)) same ((protective or	US-PGPUB;	
		<pre>(insulat\$3)) adj layer\$1 or (film\$1))) same (sidewall or (side adj wall))) same</pre>	EPO; JPO; DERWENT;	
		(sidewall or (side adj wall), same (sidewall or (side adj wall) adj mask\$1))	IBM_TDB	
		same (ion adj implant\$3)		
	·		·	

-	105	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2002/05/10 14:54
		electrode)) same ((protective or	US-PGPUB;	
		(insulat\$3)) adj layer\$1 or (film\$1))) same	EPO; JPO;	
		(sidewall or (side adj wall))) same	DERWENT;	
		(sidewall or (side adj wall) adj mask\$1)	IBM_TDB	0004/05/17 15 00
-	2009	((438/301) or (438/303) or (438/305)).CCLS.	USPAT;	2004/06/17 15:22
		((100/001) (100/001) (100/005)) (67.6	US-PGPUB	2002/05/15 11 52
-	2774	((438/301) or (438/303) or (438/305)).CCLS.	USPAT;	2002/05/15 11:53
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	0	(((438/301) or (438/303) or	USPAT;	2002/05/15 11:54
_		(438/305)).CCLS.) and (dual adj spacer) same	US-PGPUB	2002,03,13 11.31
		(implant\$3 with extension)	00 10102	!
_	0		USPAT;	2002/05/15 11:56
		(438/305)).CCLS.) and (dual adj spacer) same	US-PGPUB;	,,
		(implant\$3 with extension)	EPO; JPO;	
		,	DERWENT;	
			IBM TDB	
-	1	("6287920").PN.	USPAT;	2002/05/15 11:56
			US-PGPUB	
_	130	(((438/301) or (438/303) or	USPAT;	2002/05/15 13:51
		(438/305)).CCLS.) and (implant\$3 with	US-PGPUB;	
		extension)	EPO; JPO;	
		· · · · · · · · · · · · · · · · · · ·	DERWENT;	
İ			IBM_TDB	
-	117	(mos adj transisor) or (metal adj oxide adj	USPAT;	2002/05/16 17:05
		transistor)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	297		USPAT;	2002/05/16 17:08
ŀ		transistor)) with (plural adj dop\$3) or	US-PGPUB;	
		((first adj dop\$3) with (second adj dop\$3)	EPO; JPO;	
		with (third adj dop\$3))	DERWENT;	
			IBM_TDB	
-	4	(((mos adj transisor) or (metal adj oxide	USPAT;	2002/05/16 17:10
		adj transistor)) with (plural adj dop\$3) or	US-PGPUB;	
		((first adj dop\$3) with (second adj dop\$3)	EPO; JPO;	
		with (third adj dop\$3))) with (ion adj	DERWENT;	
		implant\$3)	IBM_TDB	2002/05/16 17:10
_	6	(((mos adj transisor) or (metal adj oxide	USPAT;	2002/05/16 17:10
1		adj transistor)) with (plural adj dop\$3) or ((first adj dop\$3) with (second adj dop\$3)	US-PGPUB; EPO; JPO;	
	1	with (third adj dop\$3)) with extension	DERWENT;	
	1	and the tentra and apply the material excension	IBM TDB	
-	11	l adj shap\$2 with sidewall\$1 and extension\$1	USPAT;	2002/10/10 11:23
		and implant\$3 and dop\$3	US-PGPUB;	,,
	1		EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	5	l adj shap\$2 with sidewall\$1 and extension\$1	USPAT;	2002/10/09 18:16
		and implant\$3 and dop\$3 and boron	US-PGPUB;	
		_	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	16		USPAT;	2002/10/09 18:16
		and dop\$3 and boron	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	
-	. 0		USPAT;	2002/10/10 11:24
		and dop\$3 and boron and boron adj florine	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	1	l add chanca with midawallda and danalantas	IBM_TDB	2002/10/10 15 5-
-	16	l adj shap\$2 with sidewall\$1 and implant\$3	USPAT;	2002/10/10 11:27
		and dop\$3 and boron	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L	<u> </u>	<u> </u>	IBM_TDB	

-	156	l adj shap\$2 and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB;	2002/10/10 11:28
			EPO; JPO; DERWENT; IBM TDB	
_	68	l adj shap\$2 and mos and implant\$3 and dop\$3 and boron	USPAT; US-PGPUB;	2002/10/10 11:49
			EPO; JPO; DERWENT;	
-	166723	l adj shap\$2 mdd with implant\$3 and boron	IBM_TDB USPAT;	2002/10/10 11:50
			US-PGPUB; EPO; JPO;	,
_	1	l adj shap\$2 and mdd with implant\$3 and	DERWENT; IBM_TDB USPAT;	2002/10/10 11:51
		boron	US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	
-	0	l adj shap\$2 with side adj wall\$ and mdd with implant\$3 and boron	USPAT; US-PGPUB;	2002/10/10 11:52
			EPO; JPO; DERWENT; IBM_TDB	
-	21	mos and mdd with implant\$3 and boron	USPAT; US-PGPUB;	2002/10/10 11:52
			EPO; JPO; DERWENT;	
-	15	pmos and mdd and boron	IBM_TDB USPAT; US-PGPUB;	2002/10/10 12:42
			EPO; JPO; DERWENT;	
-	56729	anisotrop\$\$5	IBM_TDB USPAT; US-PGPUB	2003/02/21 17:28
-	3	isostrop\$5	USPAT; US-PGPUB	2003/02/21 17:28
-	28701	isotrop\$5	USPAT; US-PGPUB	2004/06/17 18:42
-	15001	anisotrop\$\$5 and isotrop\$5	USPAT; US-PGPUB	2003/02/21 17:29
-	342575	gate (anisotrop\$\$5 and isotrop\$5) and gate	USPAT; US-PGPUB USPAT;	2003/02/21 17:29
_	39483	ion adj implant\$5	US-PGPUB USPAT;	2003/02/21 17:30
_	1875	((anisotrop\$\$5 and isotrop\$5) and gate) and	US-PGPUB USPAT;	2003/02/21 17:30
-	432112	(ion adj implant\$5) extension	US-PGPUB USPAT;	2003/02/21 17:31
-	367	(((anisotrop\$\$5 and isotrop\$5) and gate) and	US-PGPUB USPAT;	2003/02/21 17:31
-	9	(ion adj implant\$5)) and extension ("4908326" "5234850" "5501997" "5541132" "5679589" "5770508"	US-PGPUB USPAT	2003/02/21 17:57
-	2768	"5783475" "5863824" "6020242").PN. l adj shap\$2 same spacer\$1	USPAT;	2004/06/17 18:43
-	5	((((anisotrop\$\$5 and isotrop\$5) and gate) and (ion adj implant\$5)) and extension) and	US-PGPUB USPAT; US-PGPUB	2003/02/21 18:01
-	42115	(1 adj shap\$2 same spacer\$1) anisotropic or anisotropical	USPAT;	2003/05/14 09:51
_	29071	isotropic or isotropical	US-PGPUB USPAT;	2003/05/14 09:52
-	7380	(anisotropic or anisotropical) same	US-PGPUB USPAT;	2003/05/14 09:53
-	2340873	(isotropic or isotropical) side adj wall or side	US-PGPUB USPAT; US-PGPUB	2003/05/14 09:53
L			1 22 10100	L

	185606	mask	USPAT;	2003/05/14 09:53
	103000		US-PGPUB	
-	7009	(side adj wall or side) near2 mask	USPAT; US-PGPUB	2003/05/14 09:54
_	234	<pre>((anisotropic or anisotropical) same (isotropic or isotropical)) and ((side adj wall or side) near2 mask)</pre>	USPAT; US-PGPUB	2003/05/14 09:54
_	3	("5770508" "5783475" "5817563").PN.	USPAT	2003/05/14 09:57
	6	("4784965" "4855247" "5024959" "5153145" "5234850" "5472896").PN.	USPAT	2003/05/14 09:58
_	19	5770508.URPN.	USPAT	2003/05/14 09:59
_	2	6197648.URPN.	USPAT	2003/05/14 10:01
-	3802	l adj shap\$2 same spacer\$1	USPAT; US-PGPUB;	2004/06/17 13:21
			EPO; JPO; DERWENT; IBM_TDB	
-	424360	(metal adj oxide adj field adj effect adj transistor\$1)or MOS or MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/17 13:36
-	195	(l adj shap\$2 same spacer\$1) and ((metal adj oxide adj field adj effect adj transistor\$1)or MOS or MOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/17 13:37
-	4822	((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/17 18:43
-	65	(((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.) and (1 adj shap\$2 same spacer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/17 15:28